## BC817-40W

## 45 V, 0.5 A, General Purpose NPN Transistor

ON Semiconductor's BC817-40W is a General Purpose NPN Transistor that is housed in the SC-70/SOT-323 package.

## Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- This Device is $\mathrm{Pb}-$ Free, Halogen Free/BFR Free and is RoHS Compliant

MAXIMUM RATINGS $\left(\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}\right)$

| Rating | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Collector - Emitter Voltage | $\mathrm{V}_{\text {CEO }}$ | 45 | V |
| Collector - Base Voltage | $\mathrm{V}_{\text {CBO }}$ | 50 | V |
| Emitter - Base Voltage | $\mathrm{V}_{\text {EBO }}$ | 5.0 | V |
| Collector Current - Continuous | $\mathrm{I}_{\mathrm{C}}$ | 500 | mAdc |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
| :--- | :---: | :---: | :---: |
| Total Device Dissipation (Note 1) | $\mathrm{P}_{\mathrm{D}}$ | 460 | mW |
| Thermal Resistance, <br> Junction-to-Ambient (Note 1) | $\mathrm{R}_{\theta \mathrm{JA}}$ | 272 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Junction and Storage Temperature <br> Range | $\mathrm{T}_{\mathrm{J},}, \mathrm{T}_{\text {stg }}$ | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 Board, 1 oz . Cu, $100 \mathrm{~mm}^{2}$

ON Semiconductor ${ }^{\circledR}$
www.onsemi.com
COLLECTOR

MARKING DIAGRAM


CE = Specific Device Code
M = Date Code

- = Pb-Free Package
(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION $\dagger$

| Device | Package | Shipping |
| :---: | :---: | :---: |
| BC817-40WT1G | SC-70 <br> (Pb-Free) |  <br> Reel |
| NSVBC817-40WT1G | SC-70 <br> (Pb-Free) |  <br> Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS $\left(\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS |  |  |  |  |  |
| Collector-Emitter Breakdown Voltage ( $\mathrm{I} \mathrm{C}=10 \mathrm{~mA}$ ) | $\mathrm{V}_{(\mathrm{VR}) \mathrm{CEO}}$ | 45 | - | - | V |
| Collector-Emitter Breakdown Voltage $\left(\mathrm{V}_{\mathrm{EB}}=0 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=10 \mu \mathrm{~A}\right)$ | $\mathrm{V}_{\text {(VR) }}$ CES | 50 | - | - | V |
| Emitter-Base Breakdown Voltage $\left(I_{\mathrm{E}}=1.0 \mu \mathrm{~A}\right)$ | $\mathrm{V}_{(\mathrm{VR}) \text { Ebo }}$ | 5.0 | - | - | V |
| Collector Cutoff Current $\begin{aligned} & \left(\mathrm{V}_{\mathrm{CB}}=20 \mathrm{~V}\right) \\ & \left(\mathrm{V}_{\mathrm{CB}}=20 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=150^{\circ} \mathrm{C}\right) \end{aligned}$ | $\mathrm{I}_{\text {cbo }}$ | - | - | $\begin{aligned} & 100 \\ & 5.0 \end{aligned}$ | $\begin{aligned} & \mathrm{nA} \\ & \mu \mathrm{~A} \end{aligned}$ |

ON CHARACTERISTICS

| DC Current Gain (Note 2) <br> $\left(\mathrm{I}_{\mathrm{C}}=100 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=1.0 \mathrm{~V}\right)$ <br> $\left(\mathrm{IC}=500 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=1.0 \mathrm{~V}\right)$ | $\mathrm{h}_{\mathrm{FE}}$ |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: |
| 250 <br> 40 | - | - | - |  |  |
| Collector-Emitter Saturation Voltage (Note 2) <br> $\left(\mathrm{I}_{\mathrm{C}}=500 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=50 \mathrm{~mA}\right)$ | $\mathrm{V}_{\mathrm{CE} \text { (sat) }}$ | - | - | 0.7 | V |
| Base-Emitter On Voltage (Note 2) <br> $\left(\mathrm{I}_{\mathrm{C}}=500 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=1.0 \mathrm{~V}\right)$ | $\mathrm{V}_{\mathrm{BE}(\mathrm{on})}$ | - | - | 1.2 | V |

SMALL-SIGNAL CHARACTERISTICS

| Current-Gain - Bandwidth Product <br> $\left(\mathrm{I}_{\mathrm{C}}=10 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=5.0 \mathrm{~V}, \mathrm{f}=100 \mathrm{MHz}\right)$ | $\mathrm{f}_{\mathrm{T}}$ | 100 | - | - | MHz |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Output Capacitance <br> $\left(\mathrm{V}_{\mathrm{CB}}=10 \mathrm{~V}, \mathrm{f}=1.0 \mathrm{MHz}\right)$ | $\mathrm{C}_{\mathrm{obo}}$ | - | 10 | - | pF |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
2. Pulse Condition: Pulse Width $=300 \mu \mathrm{sec}$, Duty Cycle $\leq 2 \%$

## TYPICAL CHARACTERISTICS



Figure 1. DC Current Gain vs. Collector Current


Figure 3. Base Emitter Saturation Voltage vs. Collector Current


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current


Figure 4. Base Emitter Voltage vs. Collector Current


Figure 5. Current Gain Bandwidth Product vs.
Collector Current


Figure 6. Saturation Region


Figure 7. Temperature Coefficients


Figure 8. Capacitances


Figure 9. Safe Operating Area


## SCALE 4:1



NDTES:

1. DIMENSIGNING AND TQLERANCING PER ASME Y14.5M, 1982.
2. CDNTRDLLING DIMENSIDN: INCH

| DIM | MILLIMETERS |  |  | INCHES |  |  |
| :--- | :--- | :--- | :--- | :--- | :--- | :--- |
|  | MIN. | NIM. | MAX. | MIN. | NDM. | MAX. |
| A | 0.80 | 0.90 | 1.00 | 0.032 | 0.035 | 0.040 |
| A1 | 0.00 | 0.05 | 0.10 | 0.000 | 0.002 | 0.004 |
| AL | 0.70 REF |  |  | 0.028 BSC |  |  |
| b | 0.30 | 0.35 | 0.40 | 0.012 | 0.014 | 0.016 |
| c | 0.10 | 0.18 | 0.25 | 0.004 | 0.007 | 0.010 |
| D | 1.80 | 2.10 | 2.20 | 0.071 | 0.083 | 0.087 |
| E | 1.15 | 1.24 | 1.35 | 0.045 | 0.049 | 0.053 |
| e | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e1 | 0.65 BSC |  |  | 0.026 BSC |  |  |
| L | 0.20 | 0.38 | 0.56 | 0.008 | 0.015 | 0.022 |
| $H_{E}$ | 2.00 | 2.10 | 2.40 | 0.079 | 0.083 | 0.095 |



## SC-70 (SOT-323)

CASE 419
ISSUE P


XX = Specific Device Code
M = Date Code

- $\quad=$ Pb-Free Package

GENERIC
MARKING DIAGRAM

pase refer to device data sheet for actual part marking. $\mathrm{Pb}-$ Free indicator, " G " or microdot " r ", may or may not be present. Some products may not follow the Generic Marking.


CANCELLED
STYLE 2:
PIN 1. ANODE
2. N.C.

STYLE 3:
PIN 1. BASE
2. EMITTER

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE
STYLE 5:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 9 :
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. ANODE-CATHODE

STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

| DOCUMENT NUMBER: | 98ASB42819B | Electronic versions are uncontrolled except when accessed directly from the Document Repository. <br> Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |  |
| ---: | :--- | :--- | :--- |
| DESCRIPTION: | SC-70 (SOT-323) |  | PAGE 1 OF 1 |

onsemi, OnSeMi., and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application, Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that onsemi was negligent regarding the design or manufacture of the part. onsemi is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com
onsemi Website: www.onsemi.com

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components
Click to view similar products for Bipolar Transistors - Pre-Biased category:
Click to view products by ON Semiconductor manufacturer:
Other Similar products are found below :
RN1607(TE85L,F) DTA124GKAT146 DTA144WETL DTA144WKAT146 DTC113EET1G DTC115TKAT146 DTC144ECA-TP DTC144VUAT106 MUN5241T1G BCR158WH6327XTSA1 NSBA114TDP6T5G NSBA143ZF3T5G NSBC114YF3T5G NSBC123TF3T5G SMUN5235T1G SMUN5330DW1T1G SSVMUN5312DW1T2G RN1303(TE85L,F) RN4605(TE85L,F) TTEPROTOTYPE79 DDTC114EUAQ-7-F EMH15T2R SMUN2214T3G NSBC114TF3T5G NSBC143ZPDP6T5G NSVMUN5113DW1T3G SMUN5230DW1T1G SMUN5133T1G SMUN2214T1G DTC114EUA-TP NSBA144EF3T5G NSVDTA114EET1G 2SC2223-T1B-A 2SC3912-TB-E SMUN5237DW1T1G SMUN5213DW1T1G SMUN5114DW1T1G SMUN2111T1G NSVDTC144EM3T5G DTC124ECATP DTC123TM3T5G DTA114ECA-TP DTA113EM3T5G DCX115EK-7-F DTC113EM3T5G NSVMUN5135DW1T1G NSVDTC143ZM3T5G SMUN5335DW1T2G SMUN5216DW1T1G NSVMUN5312DW1T2G

